

**7NM60-U2**

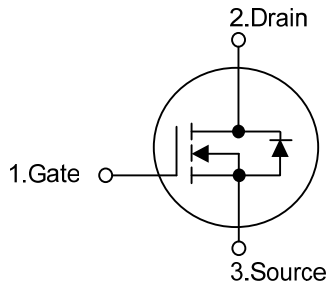
Preliminary

Power MOSFET**7.0A, 600V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The UTC **7NM60-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

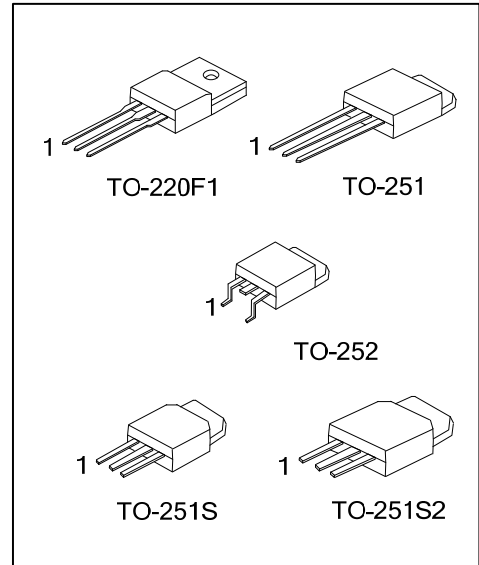
- * $R_{DS(ON)} < 0.93\Omega$ @ $V_{GS} = 10V$, $I_D = 3.5A$
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

SYMBOL**ORDERING INFORMATION**

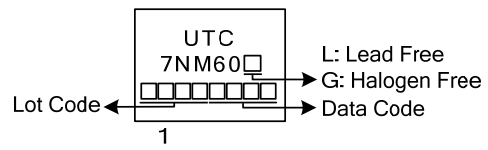
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7NM60L-TF1-T	7NM60G-TF1-T	TO-220F1	G	D	S	Tube
7NM60L-TM3-T	7NM60G-TM3-T	TO-251	G	D	S	Tube
7NM60L-TMS-T	7NM60G-TMS-T	TO-251S	G	D	S	Tube
7NM60L-TMS2-T	7NM60G-TMS2-T	TO-251S2	G	D	S	Tube
7NM60L-TN3-R	7NM60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

7NM60L-TF1-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	7.0	A
	Pulsed (Note 2)	I_{DM}	28	A
Avalanche Current (Note 2)		I_{AR}	3.4	A
Avalanche Energy		E_{AS}	130	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5.4	V/ns
Power Dissipation	TO-220F1	P_D	48	W
	TO-251/TO-251S		60	W
	TO-251S2/TO-252			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=22.5\text{mH}$, $I_{AS}=3.4\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 7.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S		110	$^\circ\text{C}/\text{W}$
	TO-251S2/TO-252			
Junction to Case	TO-220F1	θ_{JC}	2.6	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S		2.08	$^\circ\text{C}/\text{W}$
	TO-251S2/TO-252			

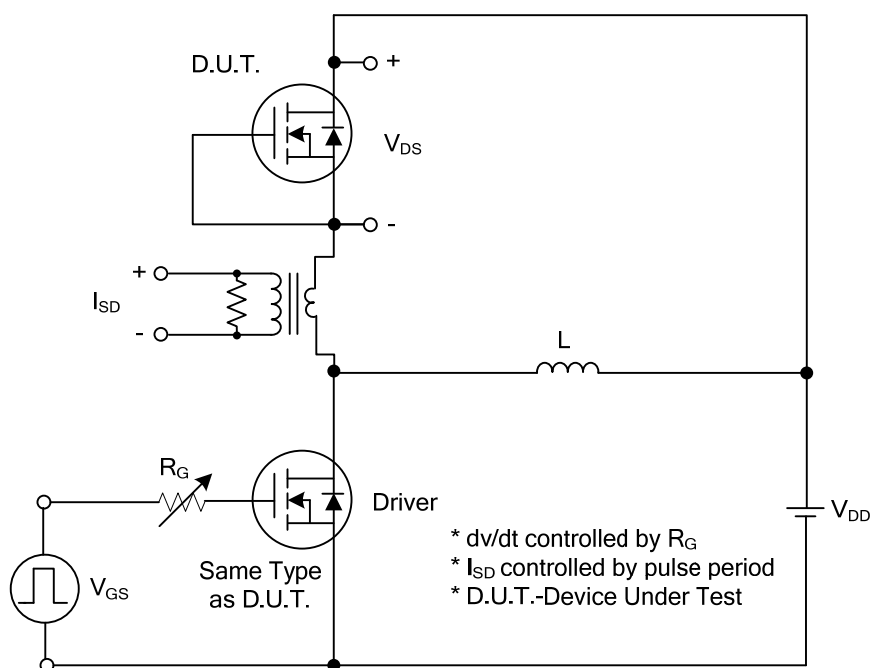
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =3.5A			0.93	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		337		pF
Output Capacitance		C _{OSS}			267		pF
Reverse Transfer Capacitance		C _{RSS}			22		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A , I _G =100μA (Note 1, 2)		51		nC
Gate to Source Charge		Q _{GS}			4.5		nC
Gate to Drain Charge		Q _{GD}			13		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		40		ns
Rise Time		t _R			49		ns
Turn-OFF Delay Time		t _{D(OFF)}			107		ns
Fall-Time		t _F			35		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				7.0	A
Maximum Body-Diode Pulsed Current		I _{SM}				28	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =7.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =7.0A, V _{GS} =0V,		255		ns
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		2.41		μC

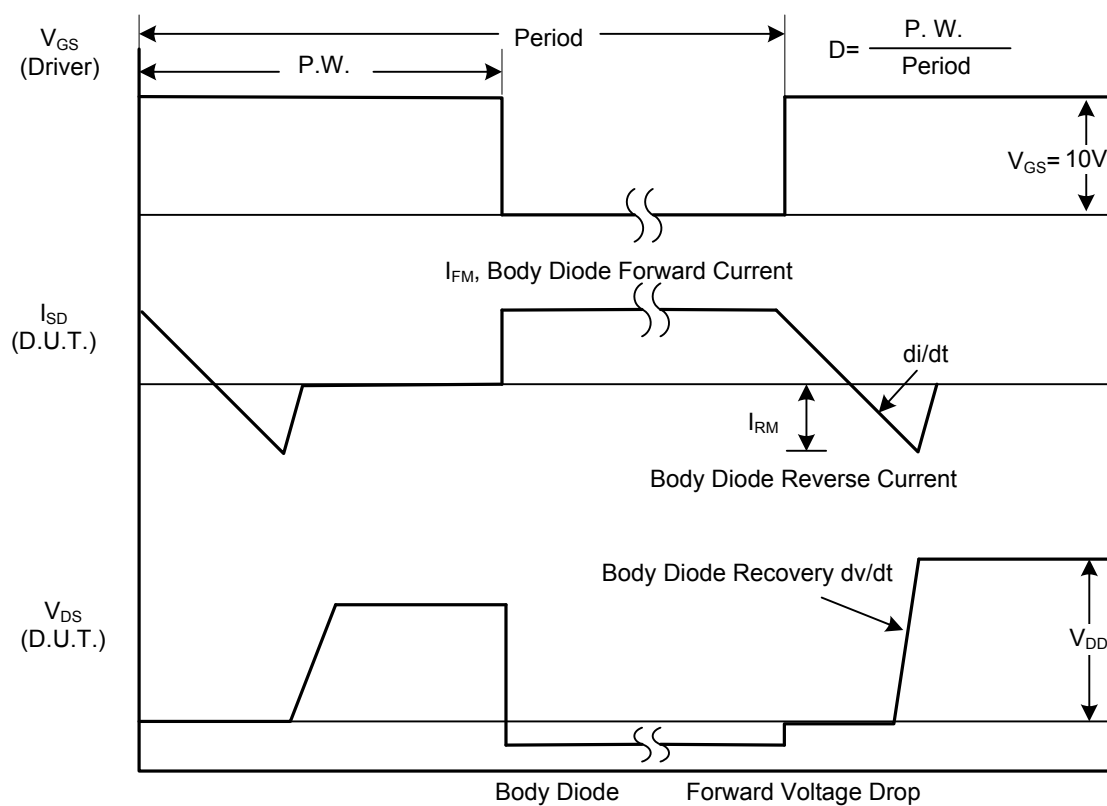
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

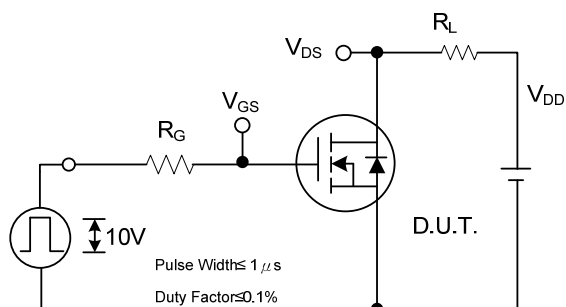


Peak Diode Recovery dv/dt Test Circuit

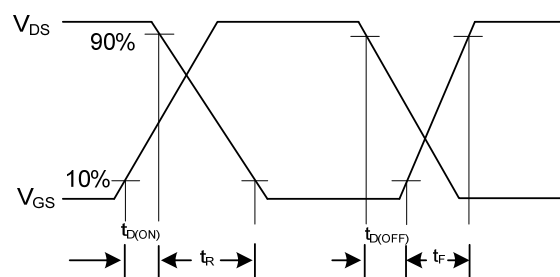


Peak Diode Recovery dv/dt Waveforms

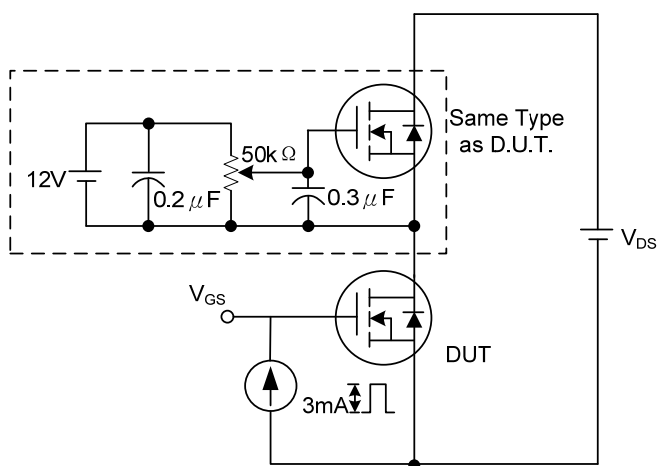
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



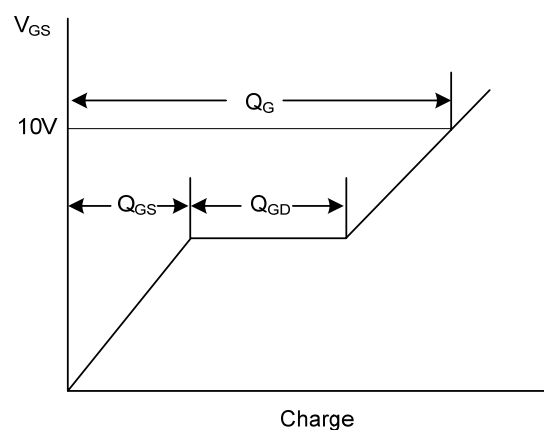
Switching Test Circuit



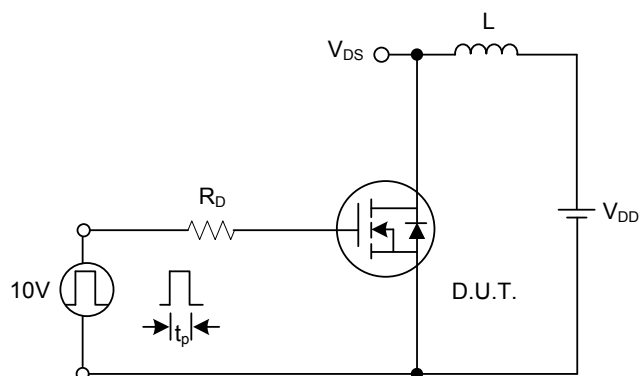
Switching Waveforms



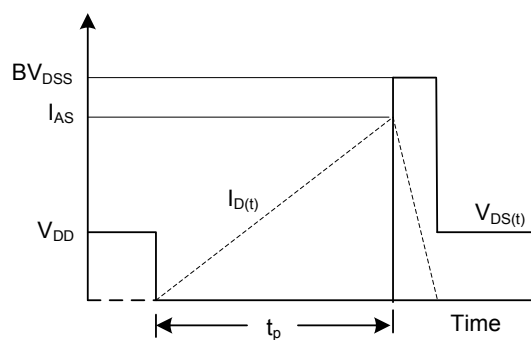
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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